

New Results of TPCs with GEMs and Pixelized Readout

J. Kaminski, University of Bonn



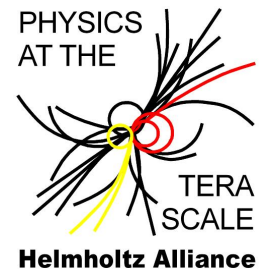
GEFÖRDERT VOM



Bundesministerium
für Bildung
und Forschung

Freiburg, 25.5.2010

5. RD51-Collaboration Meeting, WG5



Test Beam results of a TPC with a GEMs and 'pad-enlargement' Timepix chips

Christoph Brezina, Klaus Desch, Jochen Kaminski,
Martin Killenberg, Thorsten Krautscheid, Martin Schultens

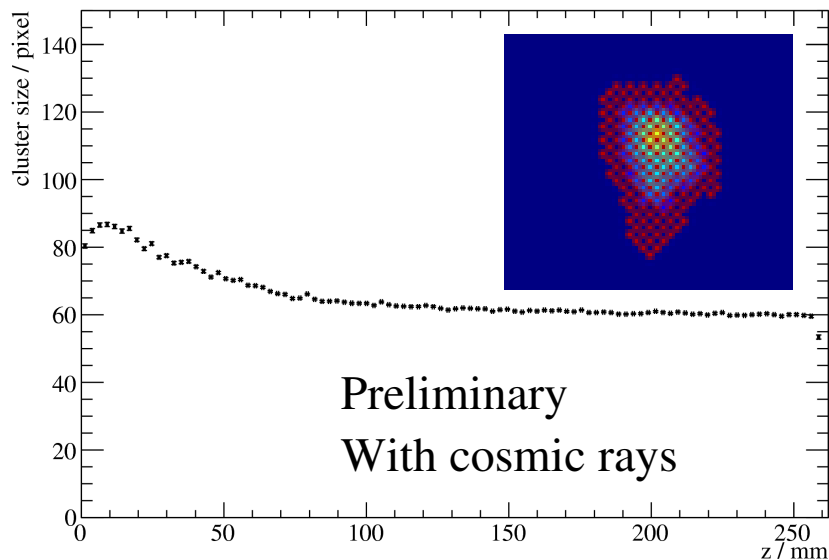
Universität Bonn

Markus Köhli, Uwe Renz, Markus Schumacher

Universität Freiburg

For more details see presentation of M. Schultens in WG7

Larger Pixel Sizes

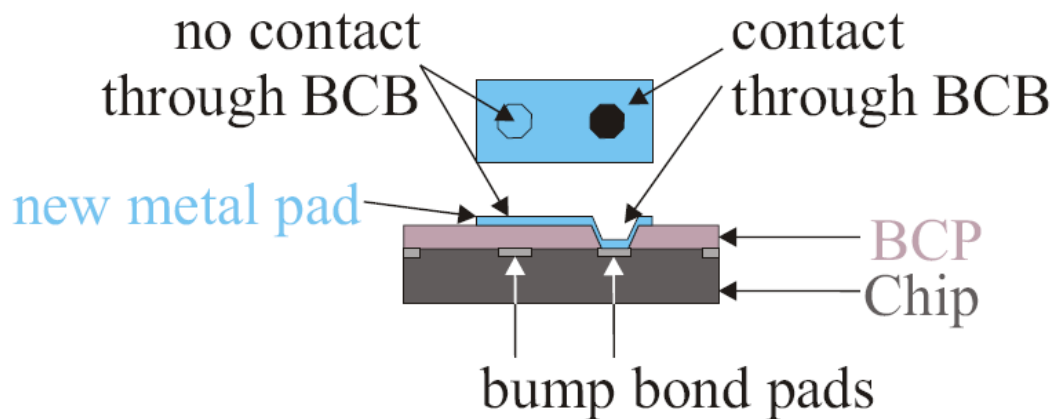


Charge depositions are spread over ~ 60 pixels
 \Rightarrow pixel sizes are too small for the charge clouds generated by a triple GEM stack
 \Rightarrow high gains (60,000 – 100,000) are necessary for the signal to pass over threshold of pixels

TEST CHIPS WITH LARGER PIXELS

expensive to design new chips

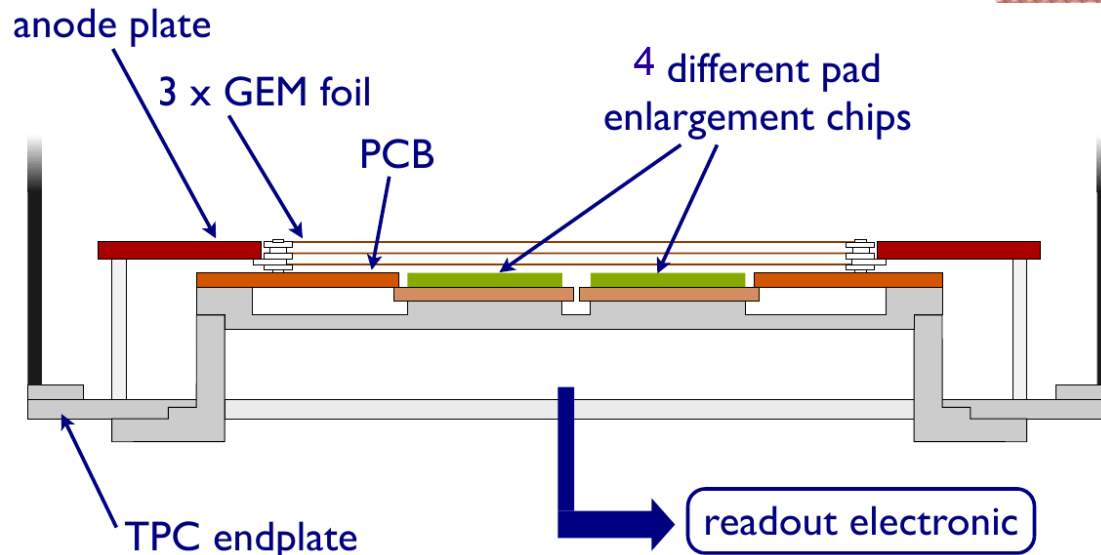
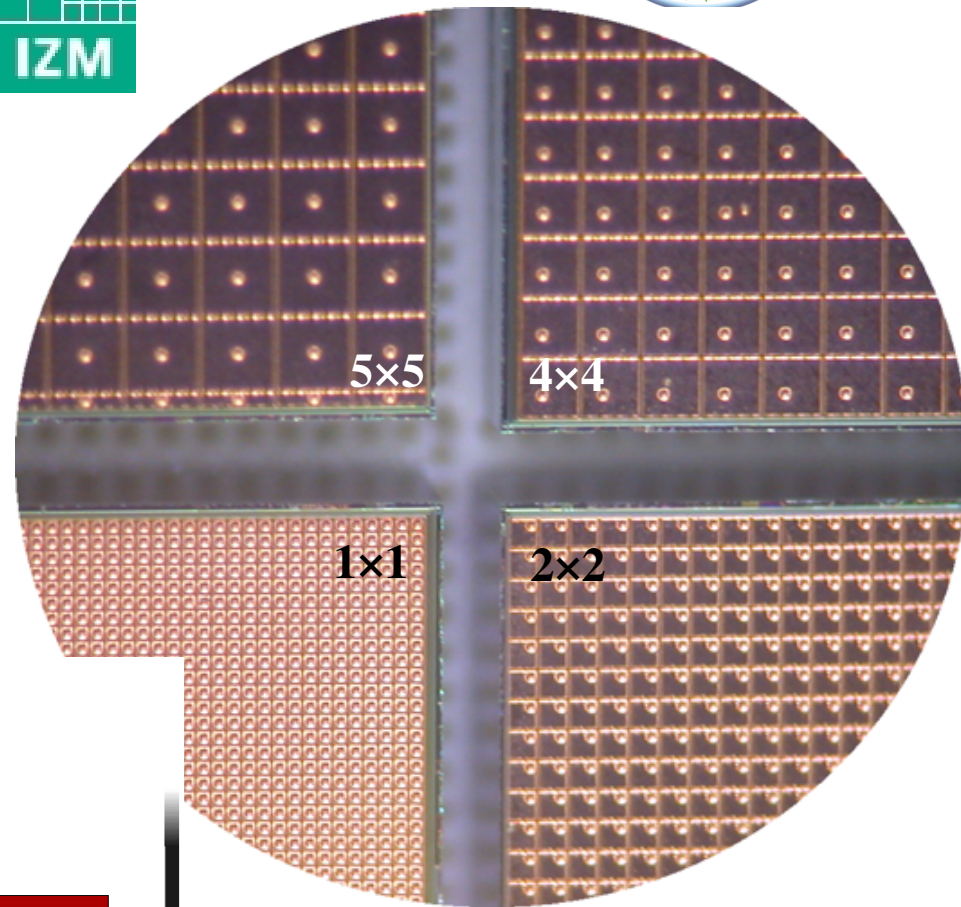
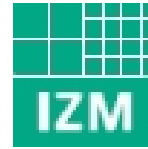
easier to combine pixels by adding new layers



Timepix with Larger Pixels



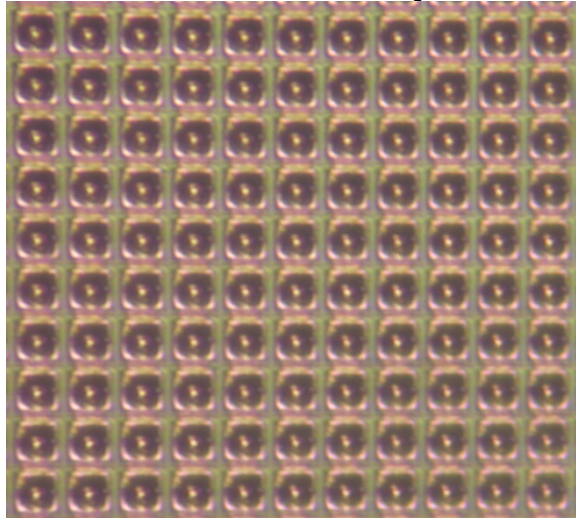
- 9 different geometries have been produced by IZM, Berlin.
- 4 have been tested during the test beam: 1×1 (for comparison), 2×2 , 4×4 , 5×5



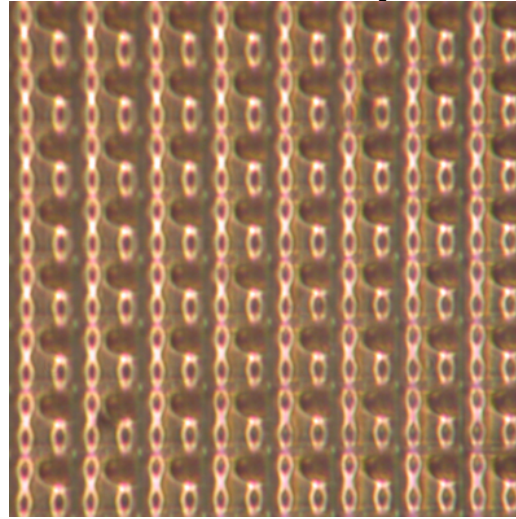
Closeup View of Chips



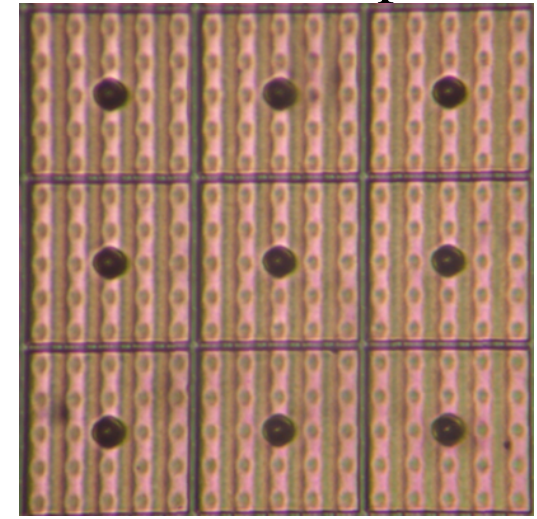
1×1-chip



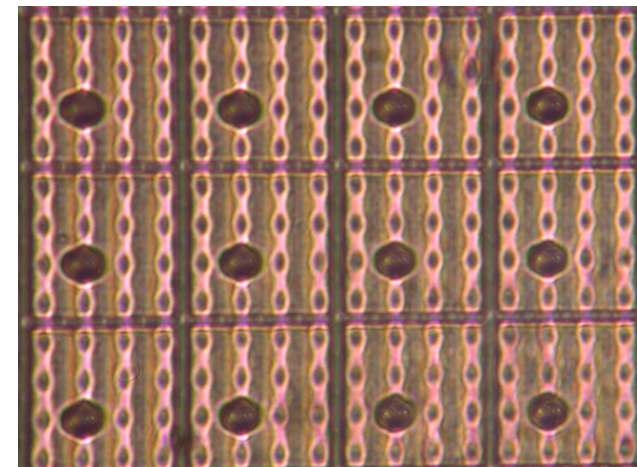
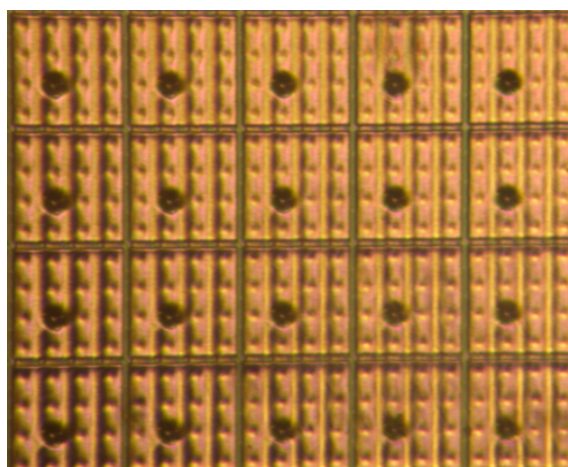
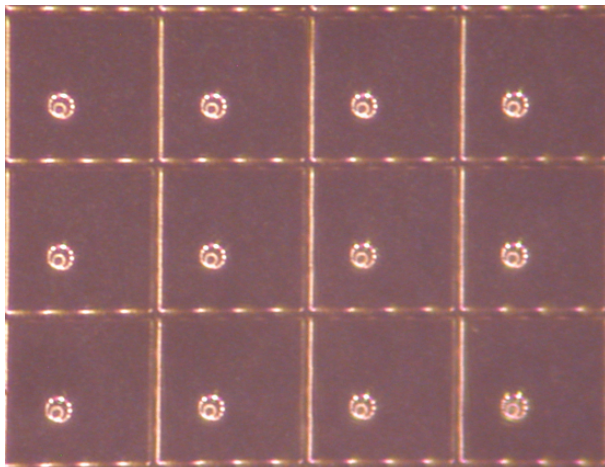
2×2-chip



5×5-chip



4×4-chip seen with different incidence of light



Setup in the Test Beam Area



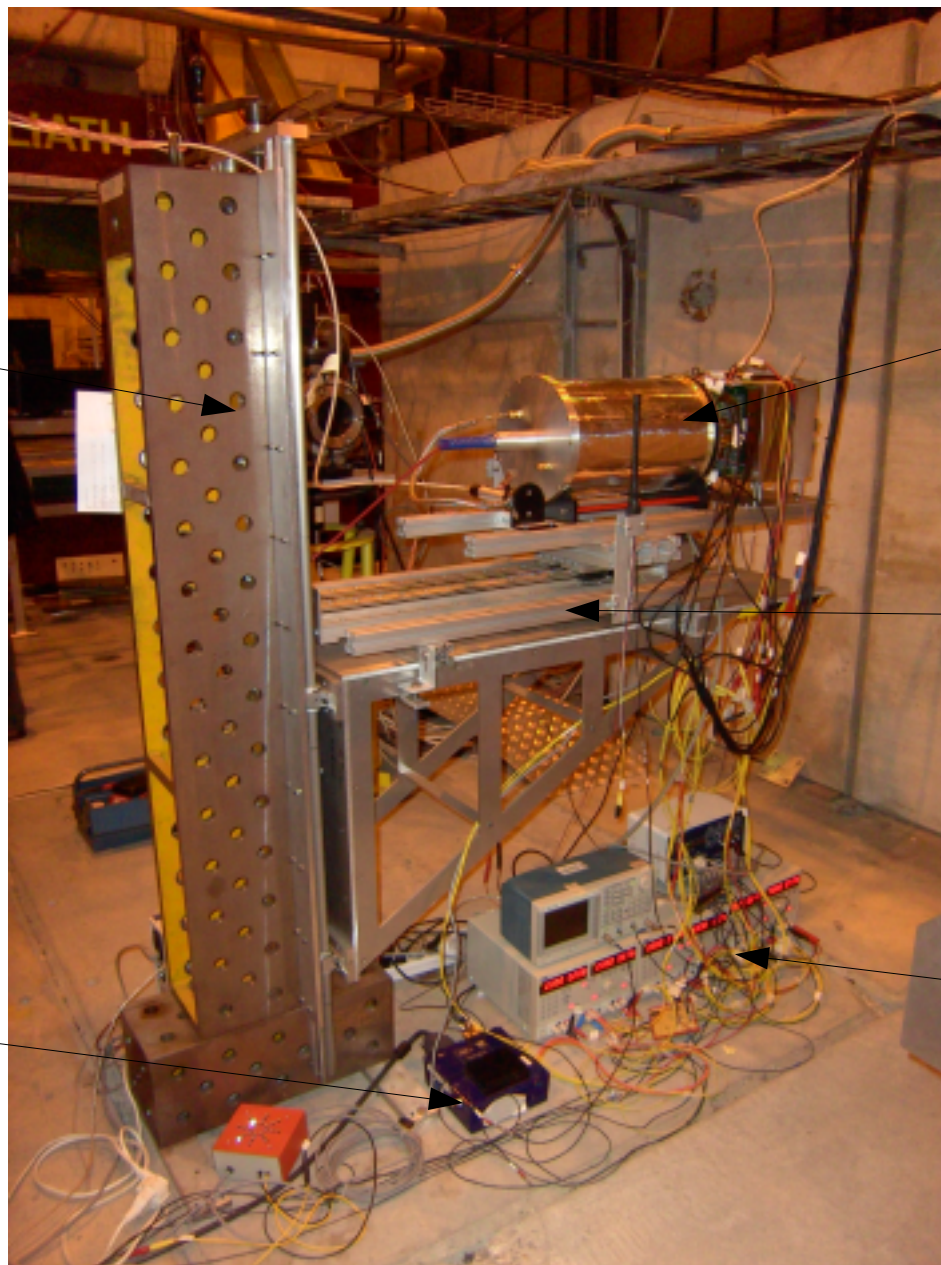
lifting stage

TPC

movable table

MUROS
Readout
electronics

LV power
supplies

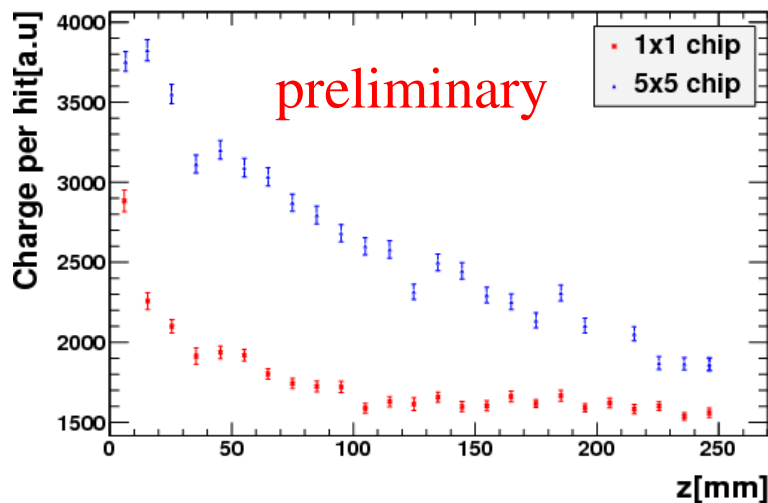


Preliminary Results

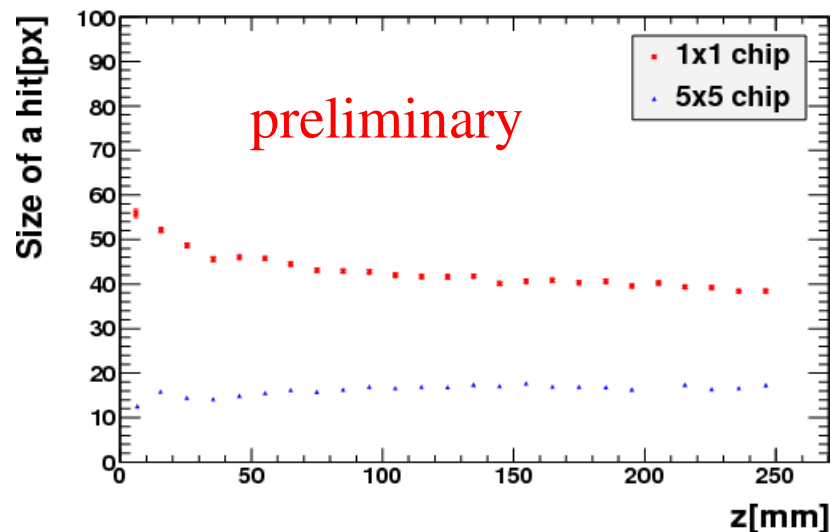


Sofar, only data from 1x1 and 5x5-chips have been analyzed.

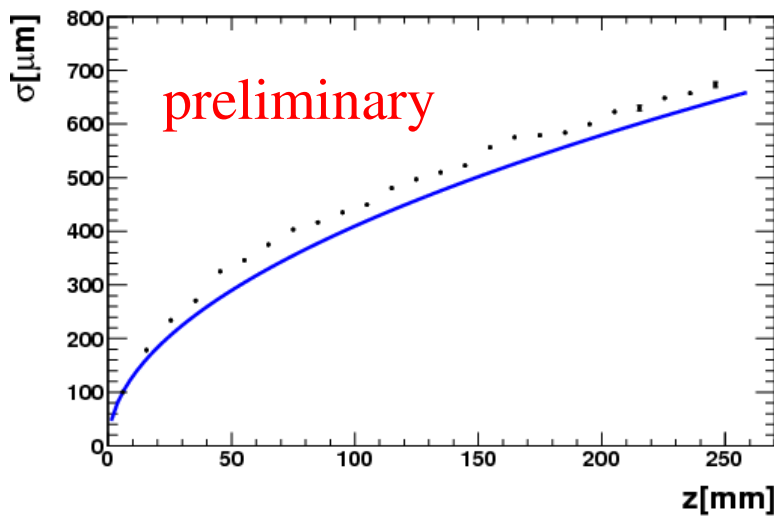
Charge per hit on track



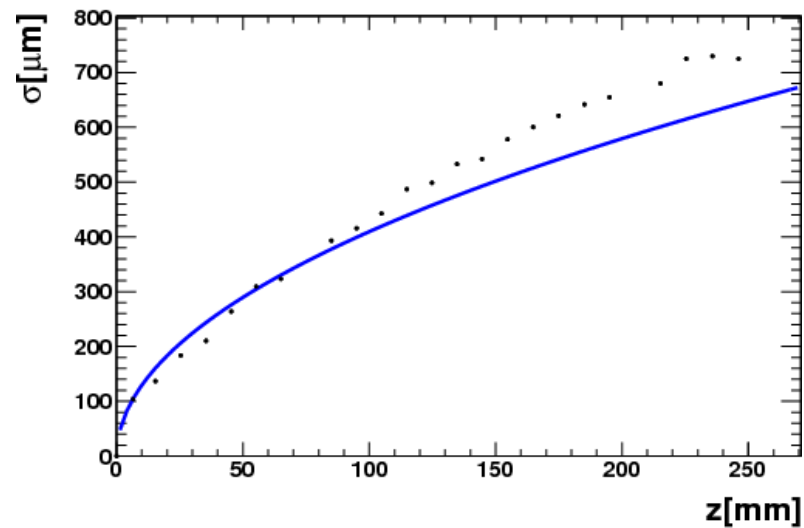
Clustersize



1x1 chip: transversal spatial resolution



5x5 chip: transversal spatial resolution



GOSSIPO3

C. Brezina, K. Desch, A. Kruth – University of Bonn
V. Gromov, R. Kluit, F. Zappone – NIKHEF / Amsterdam



GOSSIPO-3: Main Features



- Technology: 130 nm IBM CMOS
- Pixel size: $60 \times 60 \mu\text{m}^2$
- Time measurement mode or counting mode
- Drift time: up to $100 \mu\text{s}$
- Accuracy (bin size of high res. TDC): 1.7 ns
- Rise time: 20 ns
- ToT: up to $6.4 \mu\text{s}$ ($\sim 28 \text{ ke}^-$)
- ToT accuracy: 200 e^- ($\sim 27 \text{ ns}$)
- Noise: $< 70 \text{ e}^-$
- Power goal: $3 \mu\text{W}/\text{ch}$

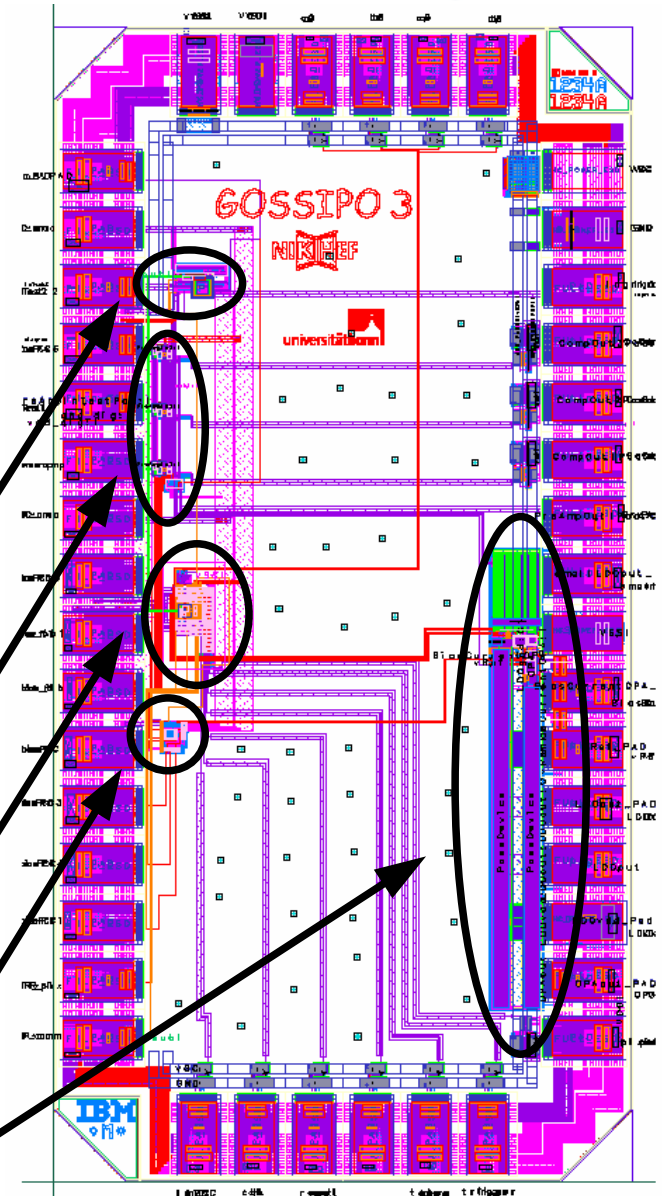
Ingrid preamp

Front-end (preamp, comp)

Pixels (Front-end, THR DAC, high res. TDC, counters, control logic)

Biasing

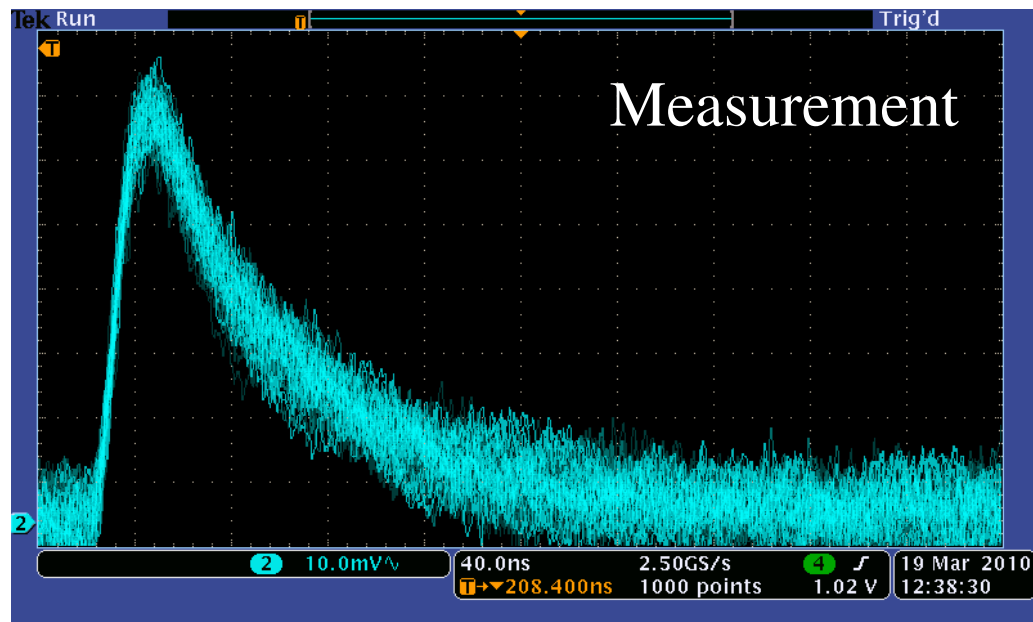
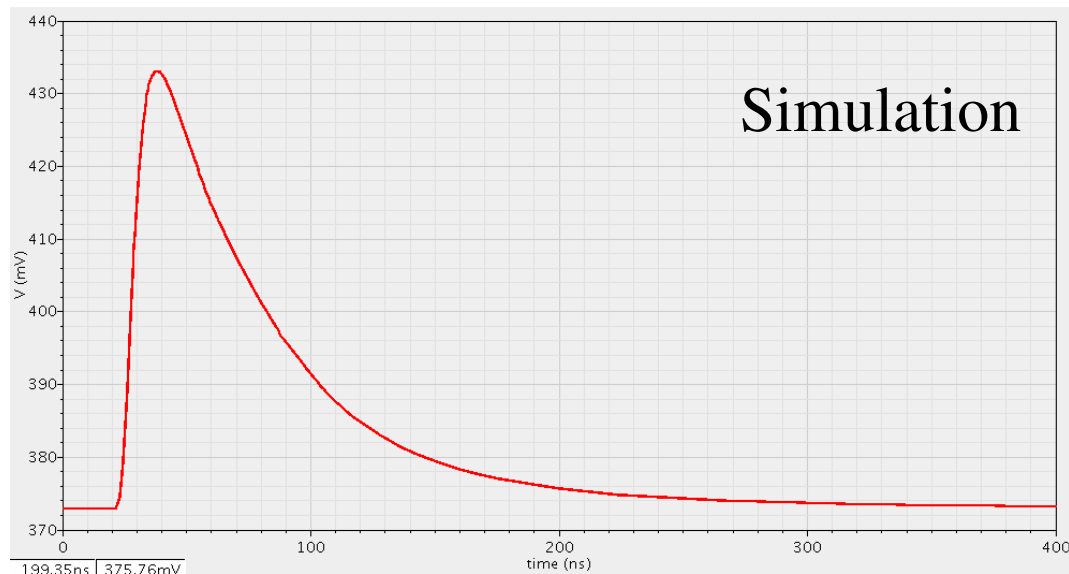
LDO (generates controllable power supply for high res. TDC)



GOSSIPO-3: Preamp Test



Preliminary

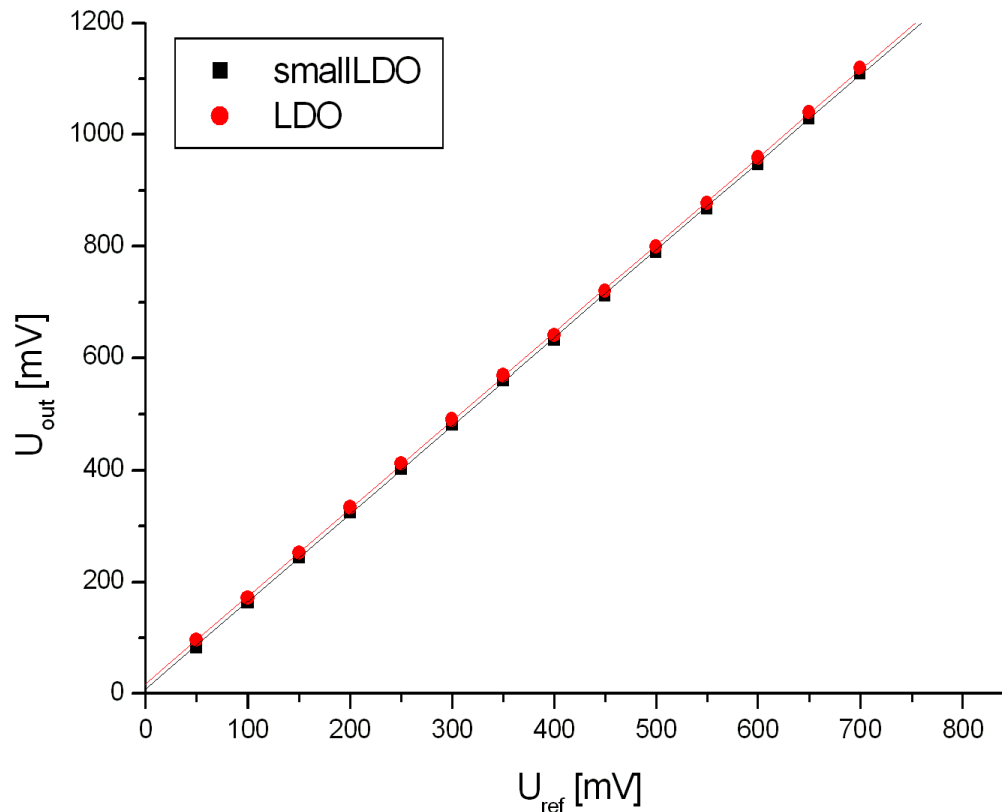


- Noise: ~ 3 mV
- Gain: ~ 120 $\mu\text{V}/e^-$
 \Rightarrow ENC ~ 25 e^-

GOSSIPO-3: LDO Linearity Test



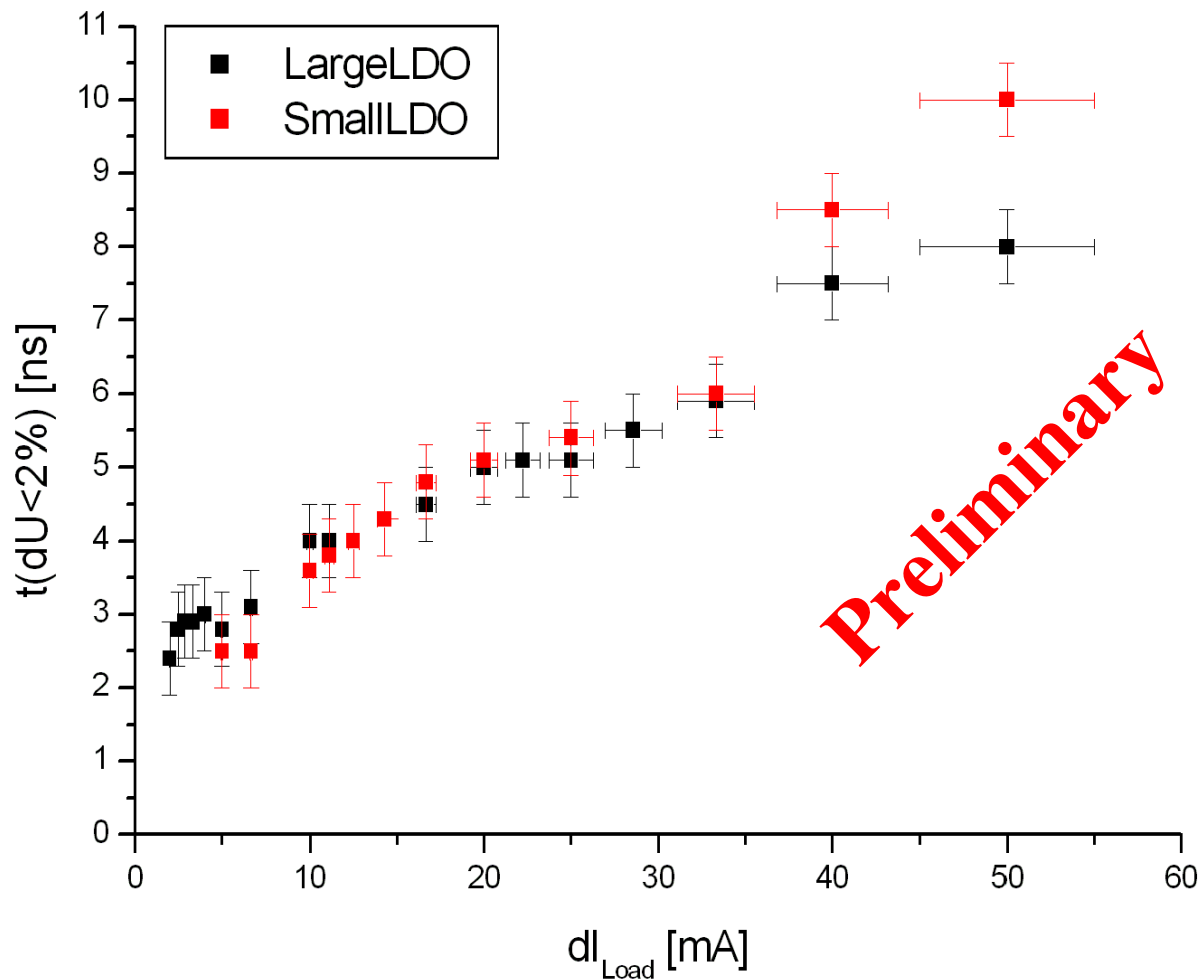
- Expected: $U_{\text{out}} = U_{\text{ref}} * (1 + R_1/R_2) = U_{\text{ref}} * 1.57$
- Measured: $U_{\text{out}} = U_{\text{ref}} * 1.57$
 - Offsets of small LDO and LDO deviate by 10mV (as expected)



GOSSIPO-3: LDO Step Response



Time needed to recover within 2% of target U_{at}



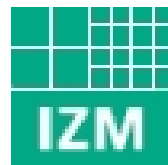
- GOSSIPO-3 is a pixelated prototype ASIC for MPGD read-out it features:
 - High resolution TDC (1.7 nsec)
 - Dynamic range up to 100 μ s
 - Low noise

- Design and testing of Chip and testboard by NIKHEF and University of Bonn

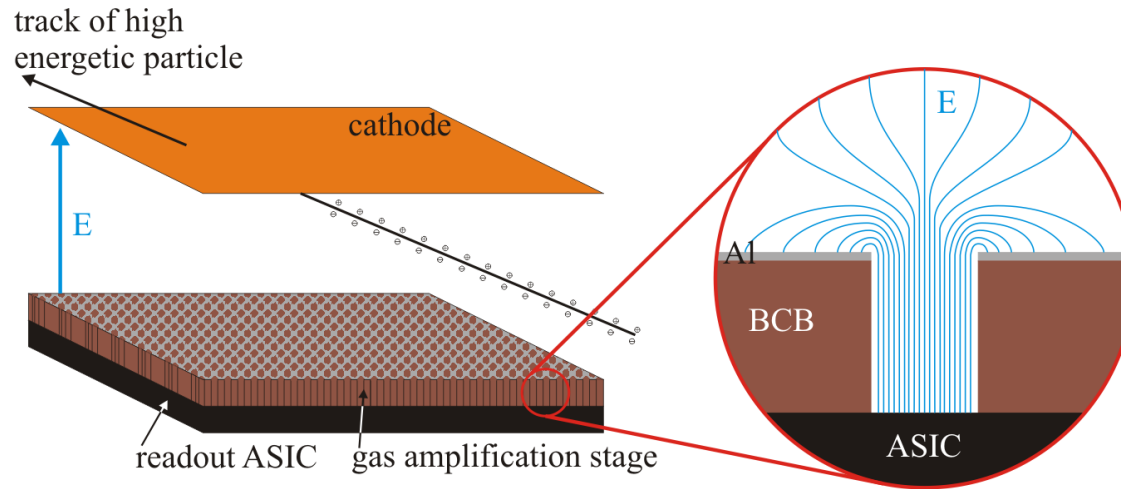
- Results will be used in Timepix2, designed within the Medipix3 collaboration

GEMGRID - Production

K. Desch, J. Kaminski, Th. Krautscheid – University of Bonn
T. Baumgartner, O. Ehrmann, Th. Fritzsch, S. Mayer, M. Töpper –
IZM, Berlin



At GEMGrid the grid does not rest on pillars like at InGrids, but on a solid insulating layer with holes.



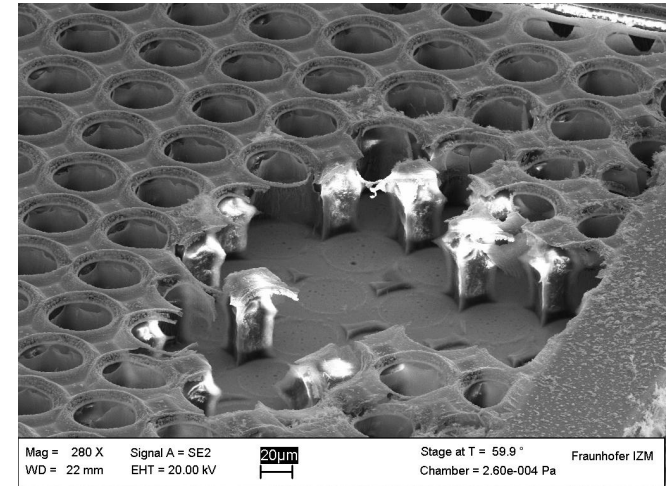
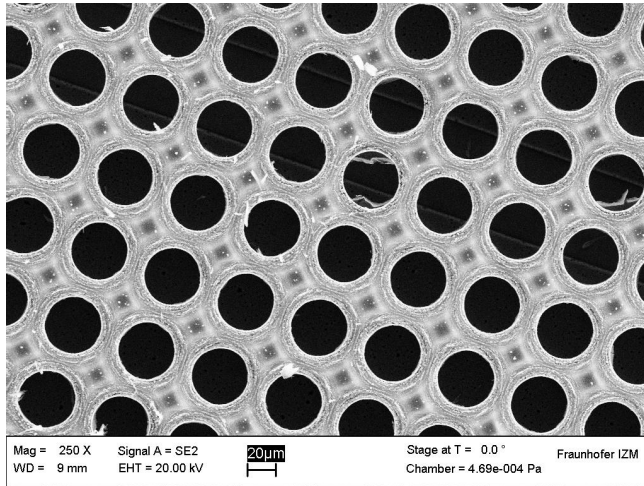
Very good InGrids have been produced at the University of Twente.

But: Productions based on single chips :-(

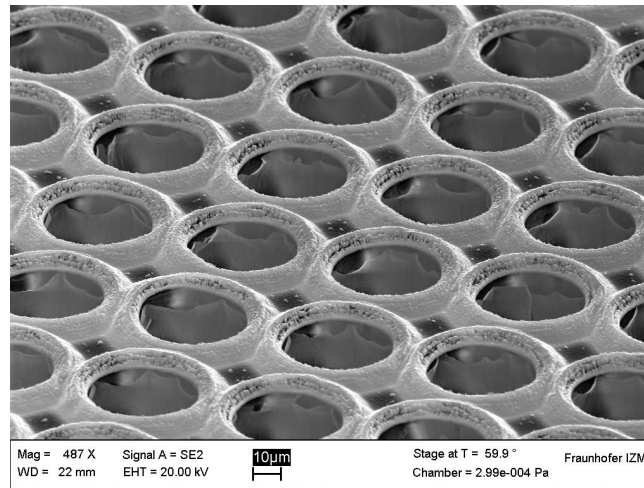
Have to transfer the knowledge to a more industrial process.

IZM at Berlin has produced a first wafer with 'dummy'-GEMGrids.
a bare Si-wafer with an aluminum pad and a GEMGrid.

SEM-Pictures of First Dummies

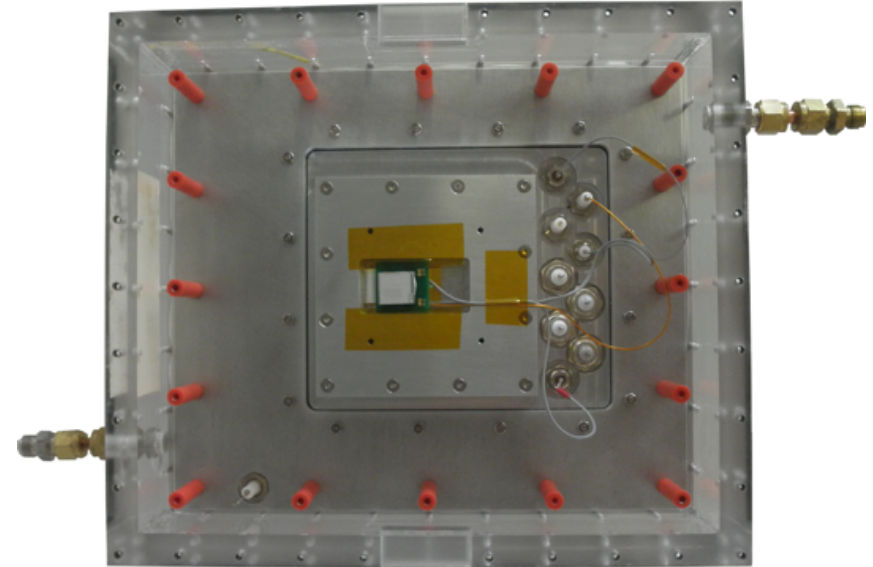
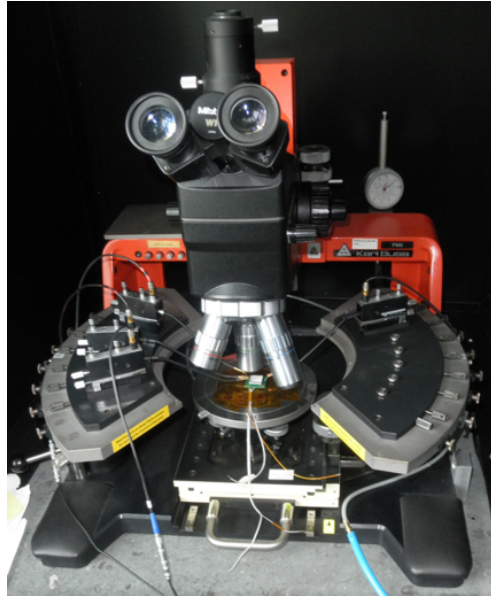
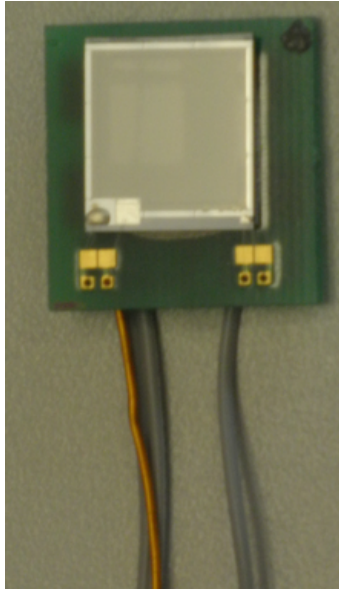


Pitch of the holes is 55 μm .



Small walls (2-3 μm)
around the holes.

First Tests – Building a Detector

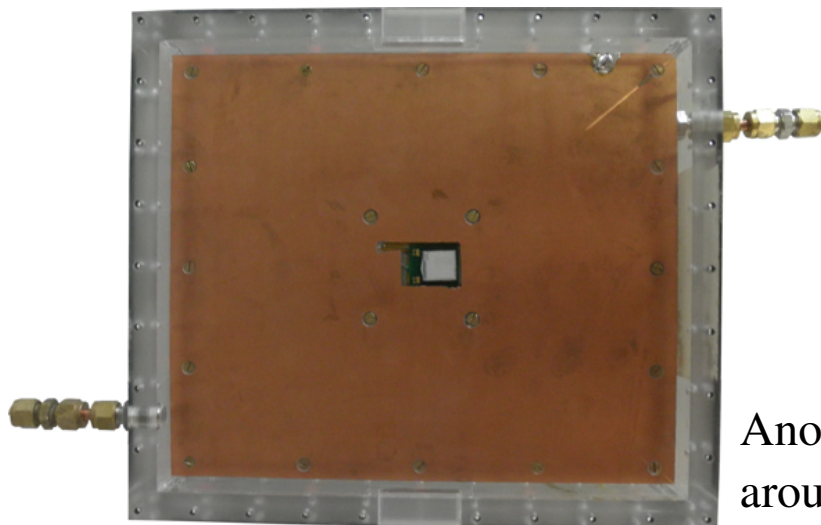
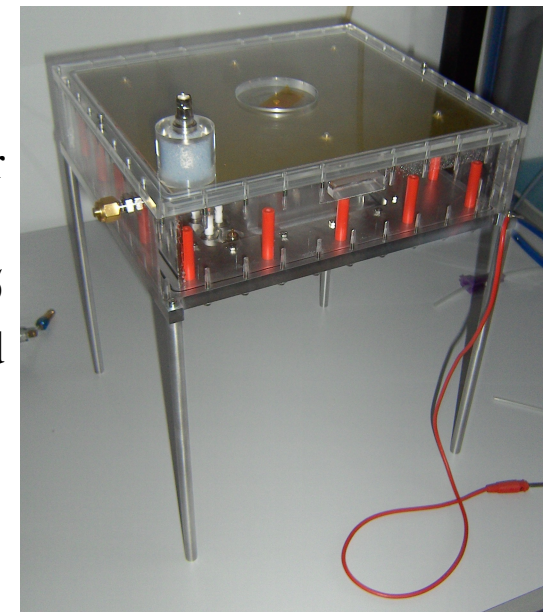


GEMGrid mounted on chip carrier.
GEMGrid placed in probing station to test leakage current.

GEMGrid placed mounted in test detector.

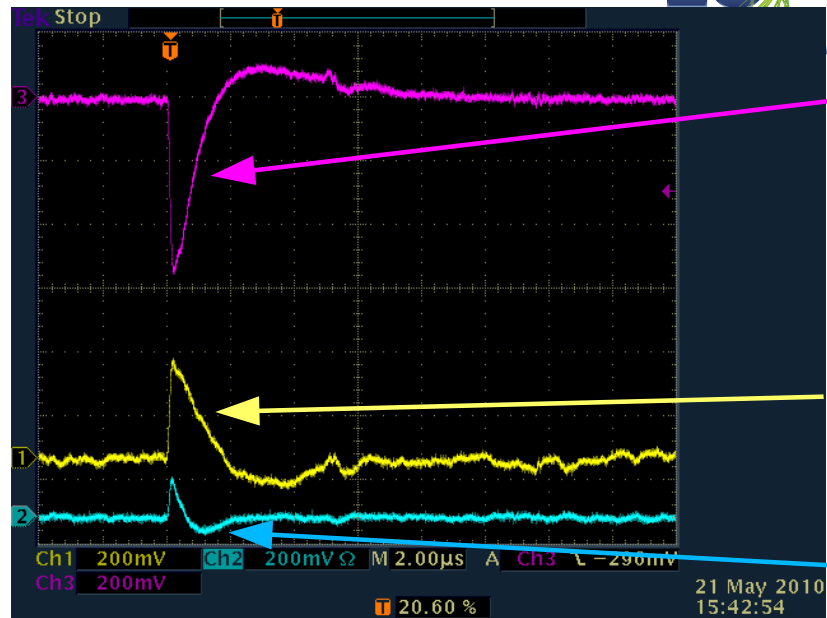
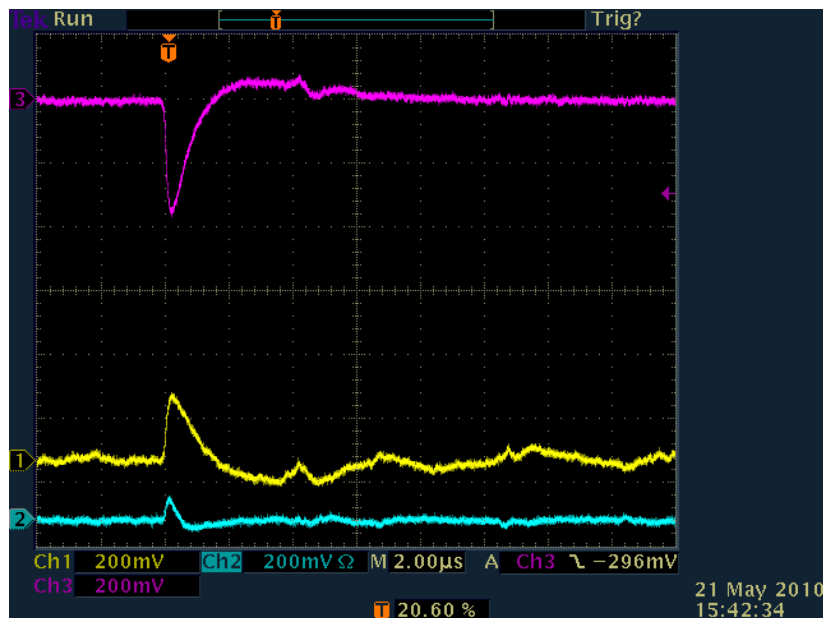
closed test
detector

Ar:iButan 95:5
315 V on grid



Anode plane placed around the GEMGrid.

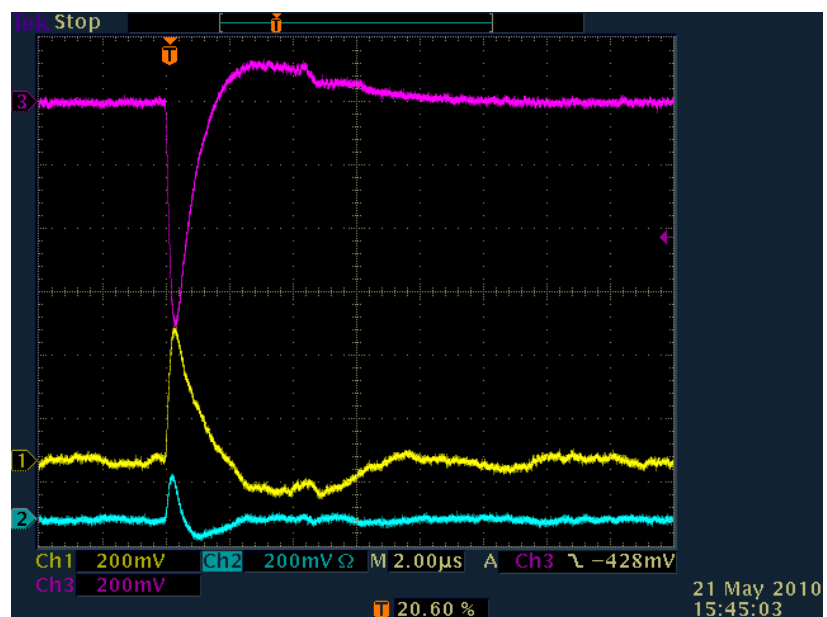
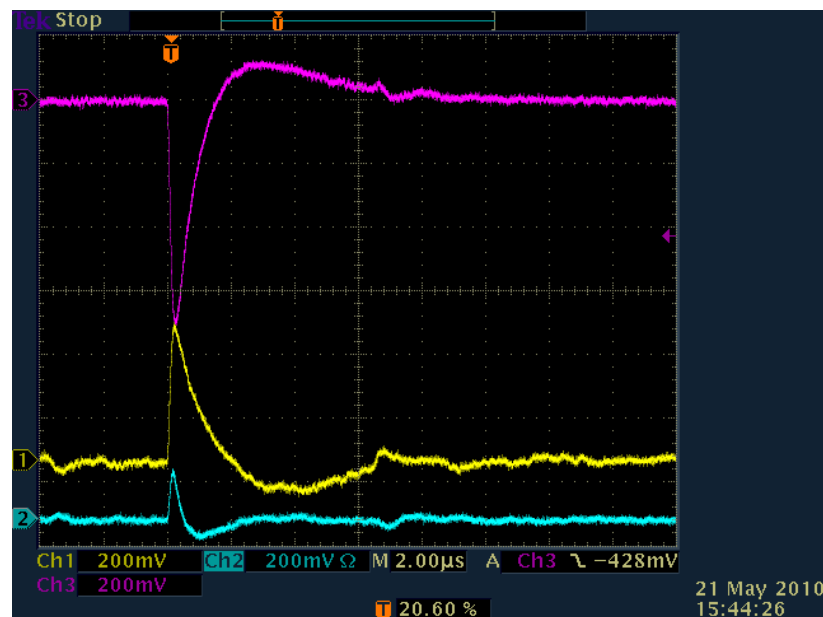
First Signals with ^{90}Sr -source



signal of grid

signal of pad

signal of ring



Rate highly correlated with rad. source!